Takeshi Kanashima

List of Publications by Year in Descending Order

86 papers	826 citations	14 h-index	24 g-index
92 ext. papers	907 ext. citations	1.8 avg, IF	3.59 L-index

#	Paper	IF	Citations
86	Electrical properties of pseudo-single-crystalline Ge films grown by Au-induced layer exchange crystallization at 250 ℃. *Journal of Applied Physics*, **2018**, 123, 215704	2.5	21
85	Robust spin-current injection in lateral spin valves with two-terminal Co2FeSi spin injectors. *AIP Advances*, **2017**, 7, 055808	1.5	2
84	A crystalline germanium flexible thin-film transistor. *Applied Physics Letters*, **2017**, 111, 222105	3.4	14
83	A low-temperature fabricated gate-stack structure for Ge-based MOSFET with ferromagnetic epitaxial Heusler-alloy/Ge electrodes. *Japanese Journal of Applied Physics*, **2016**, 55, 063001	1.4	1
82	P(VDF-TeFE)/Organic Semiconductor Structure Ferroelectric-Gate FETs. *Topics in Applied Physics*, **2016**, 187-201	0.5	
81	Exchange coupling in metallic multilayers with a top FeRh layer. *AIP Advances*, **2016**, 6, 056115	1.5	4
80	Spin transport in p-Ge through a vertically stacked Ge/Fe3Si junction. *Applied Physics Letters*, **2016**, 109, 022406	3.4	22
79	All-epitaxial Co2FeSi/Ge/Co2FeSi trilayers fabricated by Sn-induced low-temperature epitaxy. *Journal of Applied Physics*, **2016**, 119, 045302	2.5	15
78	Spin-related thermoelectric conversion in lateral spin-valve devices with single-crystalline Co2FeSi electrodes. *Applied Physics Express*, **2015**, 8, 043003	2.4	11
77	Air damping effect on the air-based CMUT operation. *Journal of the Korean Physical Society*, **2015**, 67, 486-495	0.6	
76	Low-temperature B2 ordering and magnetic properties of Fe100−xRhx films on bcc alloys. *Physical Review B*, **2015**, 92,	3.3	8
75	Effect of atomic-arrangement matching on La2O3/Ge heterostructures for epitaxial high-k-gate-stacks. *Journal of Applied Physics*, **2015**, 118, 225302	2.5	6
74	A pseudo-single-crystalline germanium film for flexible electronics. *Applied Physics Letters*, **2015**, 106, 041902	3.4	40
73	Columnar Growth of BiFeO3 Films Prepared by Magnetic-field-assisted Pulsed Laser Deposition. *Ferroelectrics*, **2014**, 466, 63-73	0.6	3
72	Current conduction in single-domain BiFeO3thin films. *Japanese Journal of Applied Physics*, **2014**, 53, 08NA01	1.4	1
71	Texture measurement and identification of object surface by MEMS tactile sensor **2014**,		3
70	Multimodal measurement of proximity and touch force by light- and strain-sensitive multifunctional MEMS sensor **2014**,		11

69	Organic ferroelectric gate field-effect transistor memory using high-mobility rubrene thin film. *Japanese Journal of Applied Physics*, **2014**, 53, 04ED11	1.4	15
68	Proximity and Tactile Sensing Using a Single MEMS Sensor with Photo- and Strain Sensitivities. *IEEJ Transactions on Sensors and Micromachines*, **2014**, 134, 229-234	0.2	8
67	Active Touch Sensing by Multi-axial Force Measurement Using High-Resolution Tactile Sensor with Microcantilevers. *IEEJ Transactions on Sensors and Micromachines*, **2014**, 134, 58-63	0.2	11
66	Preparation of epitaxial BiFeO3 thin films on La-SrTiO3 substrate by using magnetic-field-assisted pulsed laser deposition. *Journal of the Korean Physical Society*, **2013**, 62, 1041-1045	0.6	4
65	Identification of various kinds of papers using multi-axial tactile sensor with micro-cantilevers **2013**,		6
64	Force intensity and direction measurement in real time using miniature tactile sensor withl microcantilevers embedded in PDMS **2013**,		1
63	Fabrication and Noise Reduction of the Miniature Tactile Sensor Using Through-Silicon-Via Connection with Signal Amplifier. *Japanese Journal of Applied Physics*, **2013**, 52, 06GL08	1.4	10
62	Multi-axial tactile sensor with micro-cantilever embedded in hemispherical elastomer for surface texture measurement **2013**,		3
61	Repetition Rate Dependence of Ferroelectric Properties of Polycrystalline BiFeO3 Films Prepared by Pulsed Laser Deposition Method. *Ferroelectrics*, **2013**, 453, 1-7	0.6	3
60	Review of Texture Measurement of Object Surface by Tactile Sensor with Inclined Micro-cantilevers. *IEEJ Transactions on Sensors and Micromachines*, **2013**, 133, 147-154	0.2	4
59	Tactile sensor array using microcantilever with nickel□hromium alloy thin film of low temperature coefficient of resistance and its application to slippage detection. *Sensors and Actuators A: Physical*, **2012**, 186, 32-37	3.9	46
58	Heterogeneous Integration of LSI Amplifier and the Tactile Sensor Using Stacking and Through-Si-Via Techniques. *Materials Research Society Symposia Proceedings*, **2012**, 1427, 14		1
57	Ferroelectric and Piezoelectric Properties of Polycrystalline BiFeO$_{3}$ Thin Films Prepared by Pulsed Laser Deposition under Magnetic Field. *Japanese Journal of Applied Physics*, **2012**, 51, 09MD05	1.4	3
56	Organic Ferroelectric Field-Effect Transistor Memory Using Flat Poly(vinylidene fluoride□etrafluoroethylene) and Pentacene Thin Films. *Japanese Journal of Applied Physics*, **2012**, 51, 02BK06	1.4	6
55	Passivation of Ge(100) and (111) Surfaces by Termination of Nonmetal Elements. *Japanese Journal of Applied Physics*, **2012**, 51, 04DA06	1.4	1
54	Miniature Ultrasonic and Tactile Sensors for Dexterous Robot. *Transactions on Electrical and Electronic Materials*, **2012**, 13, 215-220	1.7	3
53	Fabrication of tactile sensor array using microcantilever with low-TCR nickel-chromium alloy thin film for slippage detection. *Procedia Engineering*, **2011**, 25, 627-630		1
52	Influences of perforation ratio in characteristics of capacitive micromachined ultrasonic transducers in air. *Sensors and Actuators A: Physical*, **2011**, 171, 191-198	3.9	6

51	Characterization of epitaxial BiFeO3 thin films prepared by ion beam sputtering. *Current Applied Physics*, **2011**, 11, S244-S246	2.6	7
50	Multiferroic properties of polycrystalline Zn-substituted BiFeO3 thin films prepared by pulsed laser deposition. *Current Applied Physics*, **2011**, 11, S270-S273	2.6	9
49	Mutiferroic Properties of Polycrystalline Sr-Substituted BiFeO3 Thin Films Prepared by Pulsed Laser Deposition. *Ferroelectrics*, **2011**, 416, 119-124	0.6	3
48	Improvement in the Property of Field Effect Transistor Having the HfO2/Ge Structure Fabricated by Photoassisted Metal Organic Chemical Vapor Deposition with Fluorine Treatment. *Japanese Journal of Applied Physics*, **2011**, 50, 04DA11	1.4	2
47	Fabrication of a Flexible Array for Tactile Sensors with Microcantilevers and the Measurement of the Distribution of Normal and Shear Forces. *Japanese Journal of Applied Physics*, **2011**, 50, 06GM02	1.4	5
46	Crosstalk Reduction of Tactile Sensor Array with Projected Cylindrical Elastomer over Sensing Element. *Japanese Journal of Applied Physics*, **2011**, 50, 06GM08	1.4	6
45	Preparation of BiFeO$_{3}$ Thin Films on SrRuO$_{3}$/SrTiO$_{3}$(001) Substrate by Dual Ion Beam Sputtering. *Japanese Journal of Applied Physics*, **2011**, 50, 09NB01	1.4	11
44	Preparation of BiFe$_{0.9}$Co$_{0.1}$O$_{3}$ Films by Pulsed Laser Deposition under Magnetic Field. *Japanese Journal of Applied Physics*, **2011**, 50, 09NB03	1.4	8
43	Growth of high quality BiFeO3 thin films by dual ion beam sputtering **2011**,		2
42	Structural and Ferroelectric Properties of Large c/a Phase Bismuth Ferrite Thin Films Prepared by Ion Beam Sputtering. *Materials Research Society Symposia Proceedings*, **2011**, 1292, 3		
41	Preparation and Characterization of BiFeO3 Thin Film Deposited on ITO Substrate by Using Pulsed Laser Deposition. *Journal of the Korean Physical Society*, **2011**, 59, 2537-2541	0.6	5
40	X-ray Diffraction Study of Electric-field-induced Strains in Polycrystalline BiFeO3 Thin Films at Low Temperature Using Synchrotron Radiation. *Journal of the Korean Physical Society*, **2011**, 59, 2556-2559	0.6	3
39	Structural and ferroelectric properties of epitaxial Bi5Ti3FeO15 and natural-superlattice-structured Bi4Ti3O12Bi5Ti3FeO15 thin films. *Journal of Applied Physics*, **2010**, 108, 074106	2.5	37
38	Ferroelectric Properties of Bi1.1Fe1-xCoxO3Thin Films Prepared by Chemical Solution Deposition Using Iterative Rapid Thermal Annealing in N2and O2. *Japanese Journal of Applied Physics*, **2010**, 49, 09MB05	1.4	11
37	Fabrication and Characterization of Ferroelectric Poly(vinylidene fluoride-tetrafluoroethylene) Gate Field-Effect Transistor Memories. *Japanese Journal of Applied Physics*, **2010**, 49, 04DD14	1.4	11
36	Leakage Current Reduction and Ferroelectric Property of BiFe1-xCoxO3Thin Films Prepared by Chemical Solution Deposition Using Iterative Rapid Thermal Annealing at Approximately 520 °C. *Japanese Journal of Applied Physics*, **2010**, 49, 095803	1.4	6
35	Theoretical analysis of fluorine-passivated germanium surface for high-k/Ge gate stack by molecular orbital method. *Applied Surface Science*, **2010**, 257, 917-920	6.7	6
34	Fabrication and Basic Characteristics of Multiaxial Tactile Sensor with 3 Cantilevers. *IEEJ Transactions on Sensors and Micromachines*, **2010**, 130, 223-229	0.2	9

33	Synergistic information encoding by combinatorial pulse operation of ferroelectrics. *Applied Physics Letters*, **2009**, 95, 202905	3.4	4
32	Pulsed Laser Deposition and Characterization of Sr and Zn Co-Substituted BiFeO3Thin Films. *Japanese Journal of Applied Physics*, **2009**, 48, 09KB03	1.4	27
31	Ferroelectric and structural properties of stress-constrained and stress-relaxed polycrystalline BiFeO3 thin films. *Journal of Applied Physics*, **2009**, 105, 061617	2.5	18
30	Tactle array sensor with inclined chromium/silicon piezoresistive cantilevers embedded in elastomer **2009**,		14
29	Stability Improvement of Tactile Sensor of Normal and Shear Stresses Using Ni-Cr Thin Film Gauge. *IEEJ Transactions on Sensors and Micromachines*, **2009**, 129, 411-416	0.2	21
28	ENHANCEMENT OF MEMORY RETENTION TIME OF MFIS STRUCTURE WITH SBT FERROELECTRIC AND SiO2 BUFFER LAYERS TREATED BY NITROGEN RADICAL IRRADIATION. *Integrated Ferroelectrics*, **2008**, 96, 27-39	0.8	4
27	PREPARATION AND CHARACTERIZATION OF HAFNIUM SILICATE DIELECTRIC LAYERS BY PHOTO-ASSISTED MOCVD USING MIXED PRECURSOR OF Hf(O-t-C4H9)4 AND Si(O-t-C4H9)4. *Integrated Ferroelectrics*, **2008**, 97, 103-110	0.8	2
26	Microwave Tunable Devices Composed of Coplanar Waveguide Line with (Ba0.6,Sr0.4)TiO3/Au/Cr/(Ba0.6,Sr0.4)TiO3Sandwich Structure. *Japanese Journal of Applied Physics*, **2008**, 47, 7500-7504	1.4	2
25	X-ray diffraction study of polycrystalline BiFeO3 thin films under electric field. *Applied Physics Letters*, **2008**, 93, 042907	3.4	6
24	Fabrication and Normal/Shear Stress Responses of Tactile Sensors of Polymer/Si Cantilevers Embedded in PDMS and Urethane Gel Elastomers. *IEEJ Transactions on Sensors and Micromachines*, **2008**, 128, 193-197	0.2	16
23	Characteristics improvement of HfO2/Ge gate stack structure by fluorine treatment of germanium surface. *Applied Surface Science*, **2008**, 254, 6932-6936	6.7	10
22	Development of a Microscopic Three-Axis Tactile Sensor: Preliminary Examinations to Establish Sensing Algorithm by Using a Simulated Mockup. *Lecture Notes in Computer Science*, **2008**, 561-566	0.9	2
21	FERROELECTRIC GATE FET MEMORY BASED ON CONDUCTION OF FERROELECTRIC-INSULATOR INTERFACE. *Integrated Ferroelectrics*, **2007**, 89, 160-170	0.8	2
20	Fabrication and Characterization of Silicon-Polymer Beam Structures for Cantilever-Type Tactile Sensors **2007**,		9
19	Fabrication and Characterization of Ferroelectric Gate Field-Effect Transistor Memory Based on Ferroelectric□Insulator Interface Conduction. *Japanese Journal of Applied Physics*, **2006**, 45, 8608-8610	1.4	10
18	IMPROVEMENT OF MEMORY RETENTION IN METAL-FERROELECTRIC-INSULATOR-SEMICONDUCTOR STRUCTURE BY SrBi2Ta2O9 SURFACE MODIFICATION INDUCED BY NITROGEN AND OXYGEN RADICAL IRRADIATION. *Integrated Ferroelectrics*, **2006**, 84, 179-188	0.8	5
17	Preparation and characterization of HfO2thin films by photo-assisted MOCVD. *European Physical Journal Special Topics*, **2006**, 132, 279-283		3
16	First-Principles Study of Tetragonality Ratio and Unit-Cell Volume Influence on Spontaneous Polarization of BaTiO3 and PbTiO3. *Zairyo/Journal of the Society of Materials Science, Japan*, **2006**, 55, 169-172	0.1	3

15	Preparation of fluorocarbon thin film deposited by soft X-ray ablation and its electrical characteristics and thermal stability. *Applied Surface Science*, **2006**, 252, 7774-7780	6.7	5
14	Enhancement of electrical properties in polycrystalline BiFeO3 thin films. *Applied Physics Letters*, **2006**, 89, 192902	3.4	144
13	A Trial of Smell Discrimination by SnO2 Gas Sensor. *Zairyo/Journal of the Society of Materials Science, Japan*, **2006**, 55, 165-168	0.1	2
12	Contactless Characterization of Fixed Charges in HfO2Thin Film from Photoreflectance. *Japanese Journal of Applied Physics*, **2005**, 44, 2409-2414	1.4	3
11	Characterization of Ferroelectric Thin Film/SiO2/Si Structure by Photoreflectance. *Ferroelectrics*, **2004**, 303, 119-123	0.6	
10	Basic characteristics of metal-ferroelectric-insulator-semiconductor structure using a high-k PrOx insulator layer. *Journal of Applied Physics*, **2003**, 93, 4137-4143	2.5	18
9	BURST REACTION OF THIN FILMS EXCITED BY HIGH-FLUX SOFT X-RAYS. *Surface Review and Letters*, **2002**, 09, 401-405	1.1	
8	Microfocusing of soft X-ray undulator light using an elliptically bent cylinder mirror. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2001**, 467-468, 287-290	1.2	2
7	Nondestructive and Contactless Monitoring Technique of Si Surface Stress by Photoreflectance. *Japanese Journal of Applied Physics*, **2001**, 40, 2844-2848	1.4	9
6	Molecular orbital analysis of reaction processes of fluorine with H-terminated silicon (111) and (100) surfaces. *Journal of Applied Physics*, **1999**, 85, 244-248	2.5	3
5	Electronic characterization of Si/SiO2 structure using photo-CVD SiO2 thin film on atomically flat Si substrate. *Applied Surface Science*, **1998**, 130-132, 214-220	6.7	7
4	Photoluminescence of SiO2 films grown by photo-induced chemical vapor deposition. *Applied Surface Science*, **1994**, 79-80, 321-326	6.7	21
3	Photoluminescence and Its Excimer Laser Irradiation Effects in SiO2Film Prepared by Photo-Induced Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **1993**, 32, 3113-3119	1.4	5
2	Optical characterizations of photo-induced chemical vapor deposition produced SiO2 films in vacuum ultraviolet, ultraviolet, and visible region. *Journal of Applied Physics*, **1993**, 74, 5742-5747	2.5	12
1	Molecular orbital calculation of surface reaction of SnO/sub 2/ gas sensors for aminic and carboxylic smells		1